

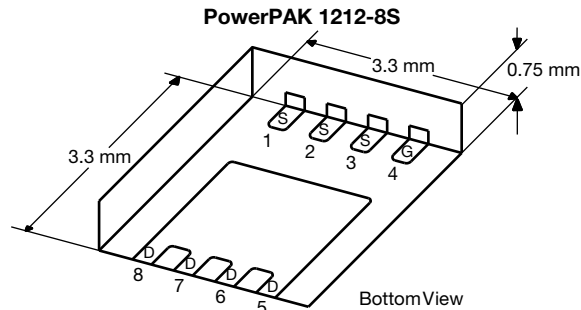


**THE DATASHEET OF  
SIS888DN-T1-GE3**



## N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) (MAX.)	I <sub>D</sub> (A) <sup>f</sup>	Q <sub>g</sub> (TYP.)
150	0.058 at V <sub>GS</sub> = 10 V	20.2	7.6 nC
	0.085 at V <sub>GS</sub> = 7.5 V	16.6	



Ordering Information:  
SiS888DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

### FEATURES

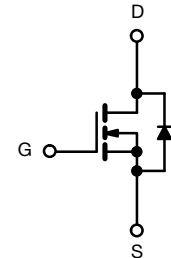
- ThunderFET® technology optimizes balance of R<sub>DS(on)</sub>, Q<sub>g</sub>, Q<sub>sw</sub> and Q<sub>oss</sub>
- 100 % R<sub>g</sub> and UIS tested
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Primary side switch
- Synchronous rectification
- DC/DC conversion
- Load switching
- Boost converters
- DC/AC inverters



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V <sub>DS</sub>	150	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	20.2	A	
	T <sub>C</sub> = 70 °C	16		
	T <sub>A</sub> = 25 °C	5.3 <sup>a,b</sup>		
	T <sub>A</sub> = 70 °C	4.3 <sup>a,b</sup>		
Pulsed Drain Current (t = 300 μs)	I <sub>DM</sub>	50		
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	40 <sup>g</sup>		
	T <sub>A</sub> = 25 °C	3.1 <sup>a,b</sup>		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	10	
Single Pulse Avalanche Energy		E <sub>AS</sub>	5	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	52	W
	T <sub>C</sub> = 70 °C		33	
	T <sub>A</sub> = 25 °C		3.7 <sup>a,b</sup>	
	T <sub>A</sub> = 70 °C		2.4 <sup>a,b</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150		°C
Soldering Recommendations (Peak Temperature) <sup>c,d</sup>		260		

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient <sup>a,e</sup>	t ≤ 10 s	R <sub>thJA</sub>	26	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	1.9	

#### Notes

- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK 1212-8S is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 81 °C/W.
- Based on T<sub>C</sub> = 25 °C.
- Package limited.



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	150			V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA		97		mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>			-6.9		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	3		4.2	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	20			A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		0.048	0.058	Ω
		V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 7 A		0.066	0.085	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		11		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 0 V, f = 1 MHz		420		pF
Output Capacitance	C <sub>OSS</sub>			130		
Reverse Transfer Capacitance	C <sub>RSS</sub>			16		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		9.5	14.5	nC
		V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 10 A		7.6	11.5	
Gate-Source Charge	Q <sub>gs</sub>			2.5		
Gate-Drain Charge	Q <sub>gd</sub>			3.6		
Output Charge	Q <sub>OSS</sub>	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 0 V		23.6	36	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.4	1.3	2	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 75 V, R <sub>L</sub> = 7.5 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 7.5 V, R <sub>g</sub> = 1 Ω		13	26	ns
Rise Time	t <sub>r</sub>			11	22	
Turn-Off Delay Time	t <sub>d(off)</sub>			14	28	
Fall Time	t <sub>f</sub>			9	18	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 75 V, R <sub>L</sub> = 7.5 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω		12	24	
Rise Time	t <sub>r</sub>			8	16	
Turn-Off Delay Time	t <sub>d(off)</sub>			13	26	
Fall Time	t <sub>f</sub>			8	16	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			40	A
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				50	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 4 A, V <sub>GS</sub> = 0 V		0.85	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C		94	180	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			190	380	nC
Reverse Recovery Fall Time	t <sub>a</sub>			35		ns
Reverse Recovery Rise Time	t <sub>b</sub>			59		

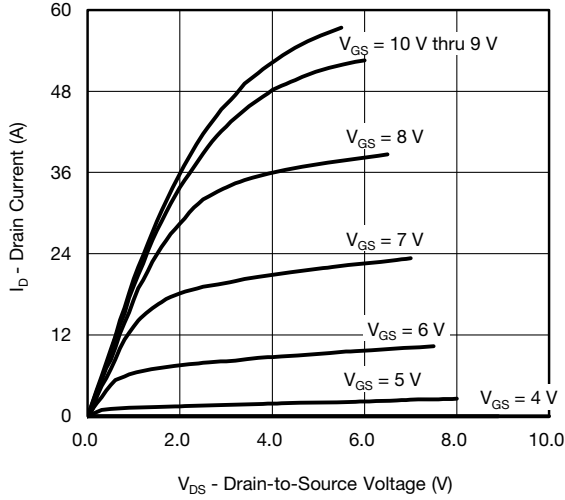
**Notes**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

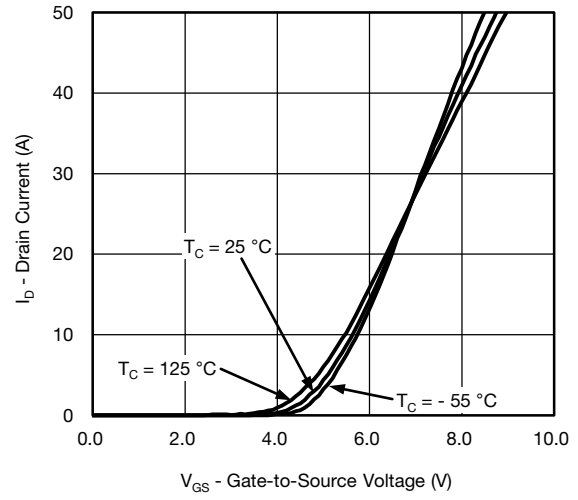
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



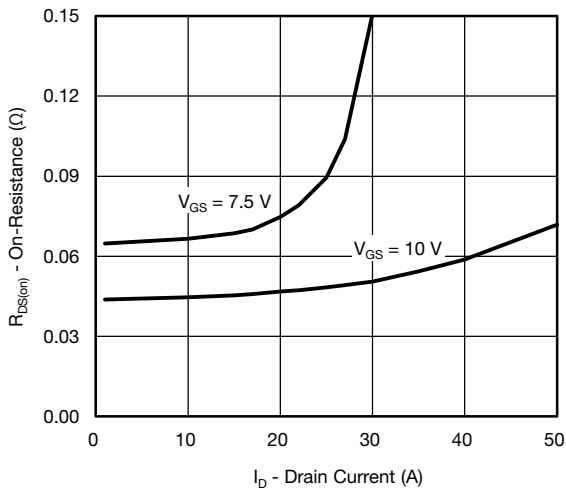
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



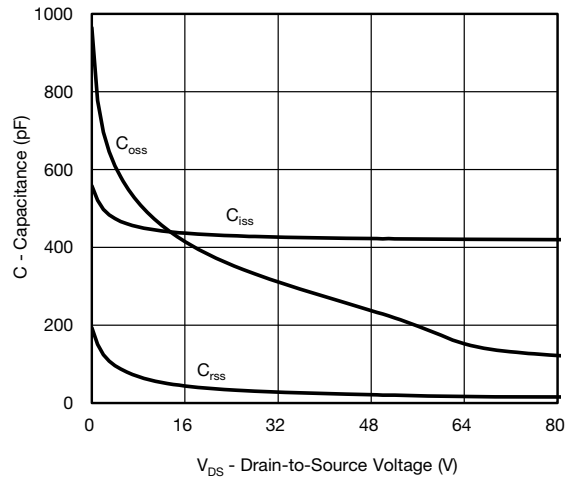
Output Characteristics



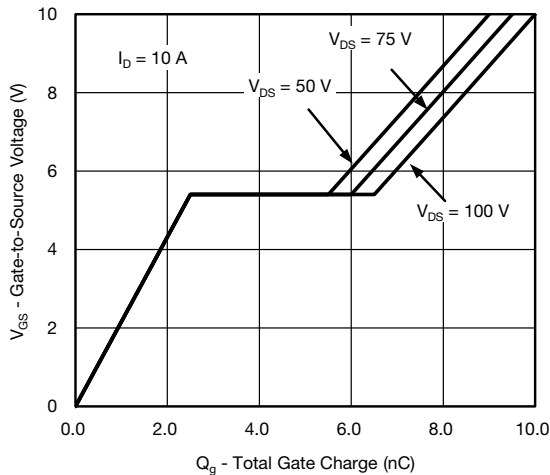
Transfer Characteristics



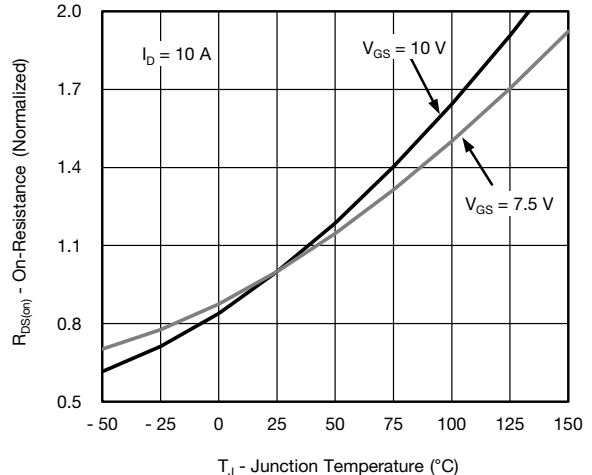
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



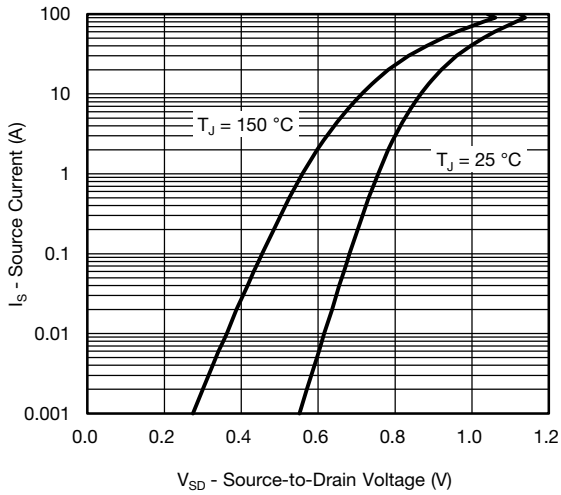
Gate Charge



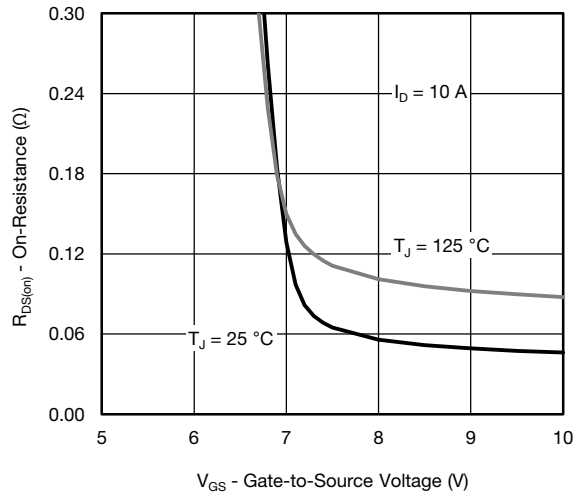
On-Resistance vs. Junction Temperature



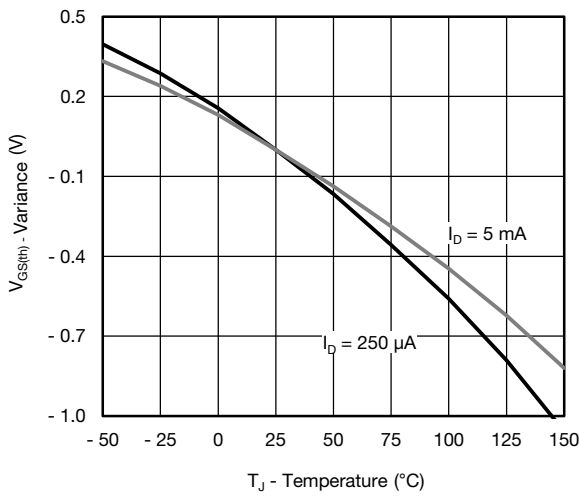
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



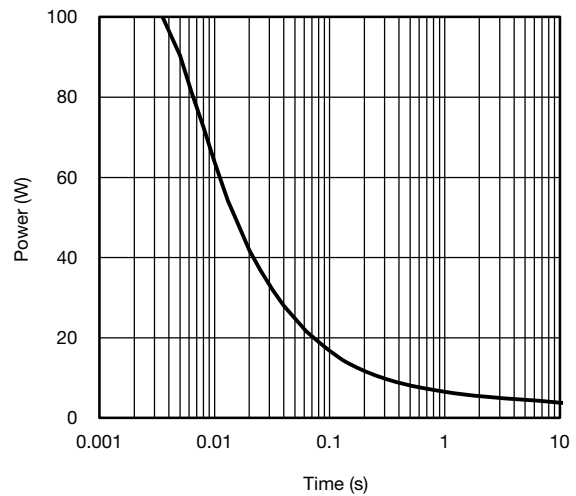
Source-Drain Diode Forward Voltage



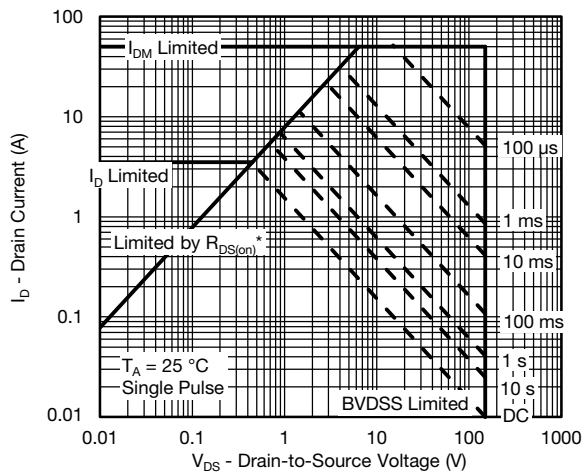
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



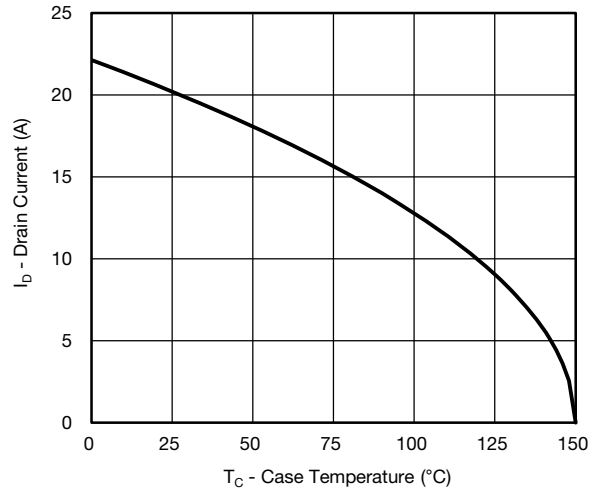
Single Pulse Power, Junction-to-Ambient



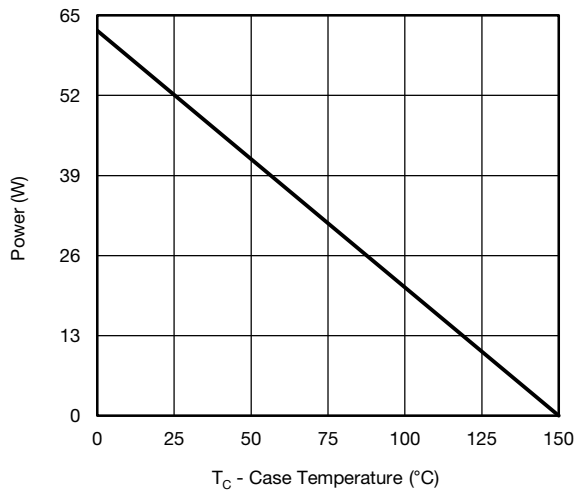
Safe Operating Area, Junction-to-Ambient



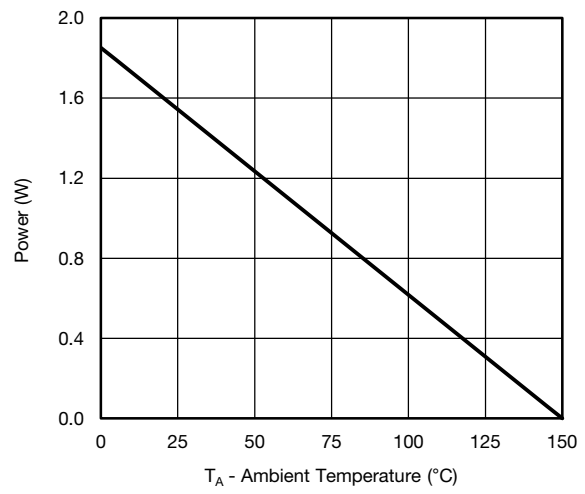
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating\***



**Power, Junction-to-Case**

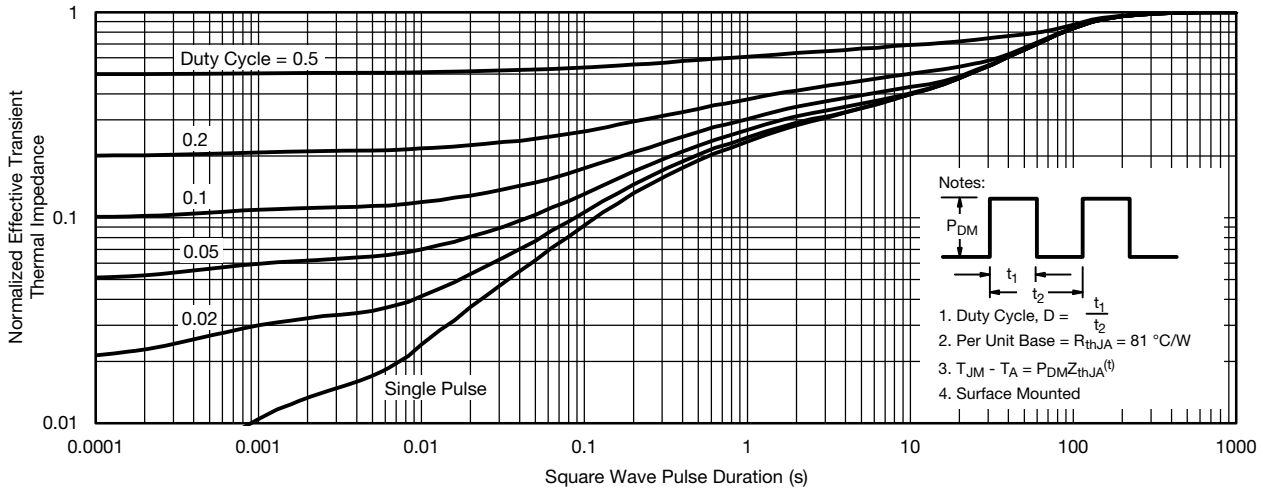


**Power, Junction-to-Ambient**

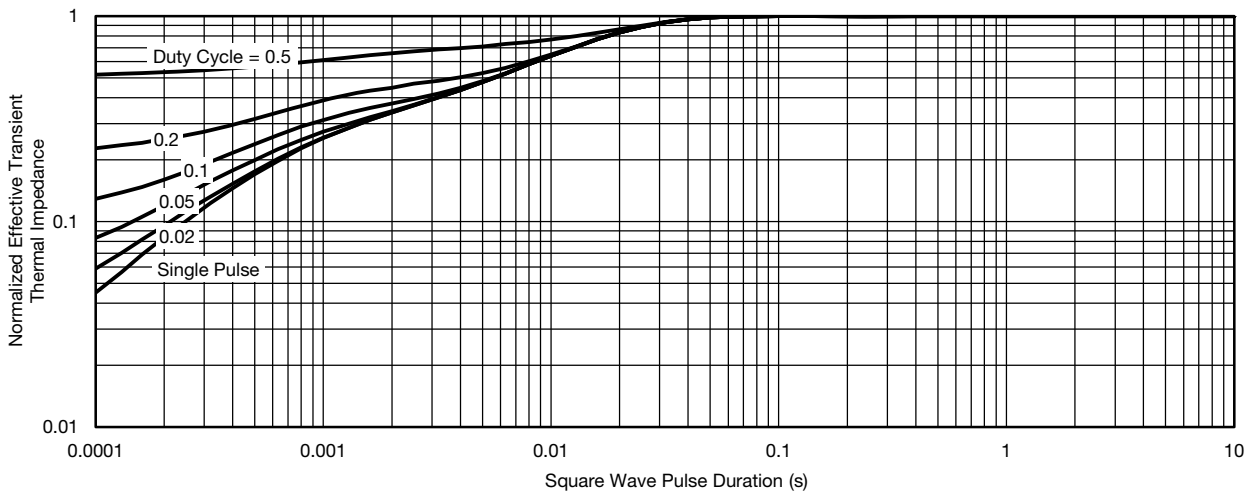
\* The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



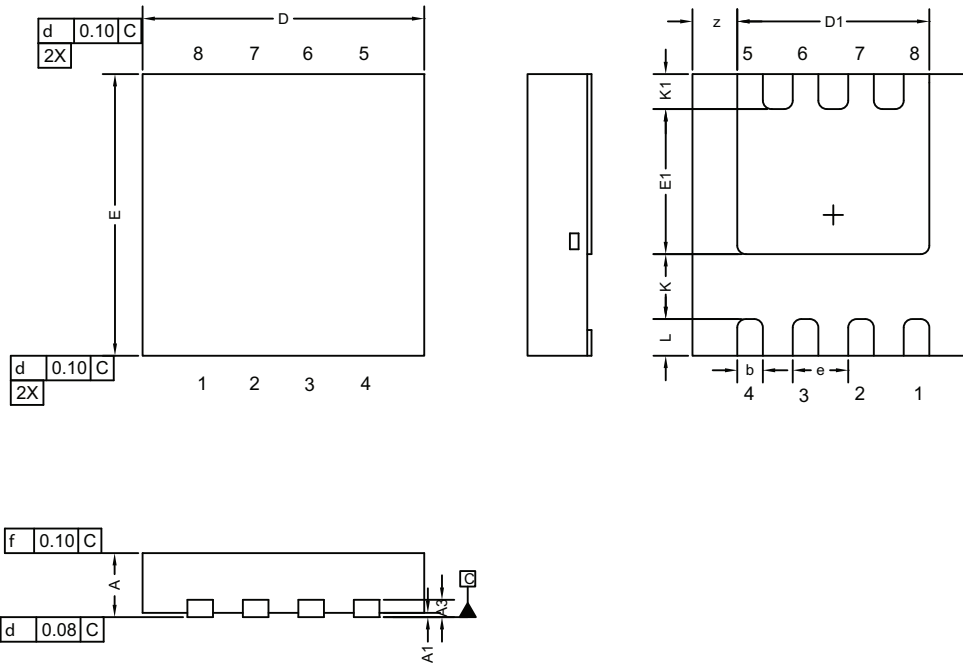
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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## Case Outline for PowerPAK® 1212-8S



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.67	0.75	0.83	0.027	0.030	0.033
A1	0	-	0.05	0	-	0.002
A3	0.20 REF			0.008 REF		
b	0.30 BSC			0.012 BSC		
D	3.30 BSC			0.130 BSC		
D1	2.15	2.25	2.35	0.084	0.088	0.092
E	3.30 BSC			0.130 BSC		
E1	1.60	1.70	1.80	0.063	0.067	0.071
e	0.65 BSC			0.026 BSC		
K	0.76 TYP			0.030 TYP		
K1	0.41 TYP			0.016 TYP		
L	0.43 BSC			0.017 BSC		
z	0.525 TYP			0.021 TYP		
ECN: C12-0200-Rev. A, 12-Mar-12						
DWG: 6008						

### Note

- Millimeters will govern.

## RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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